

**PROCESS FOR FABRICATING LOW LEAKAGE CURRENT
ELECTRODE FOR LPCVD TITANIUM OXIDE FILMS**

ABSTRACT OF THE DISCLOSURE

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A process for fabricating electrodes for the capacitor dielectric of semiconductor memory devices with low leakage current characteristics is disclosed. The process comprises the steps of first depositing a titanium oxide film over a semiconductor silicon substrate. The deposited titanium oxide film is then
10 annealed. A layer of tungsten nitride top electrode is then deposited on the annealed titanium oxide film. A second annealing procedure is then conducted to simulate post electrode high temperature process.

Fig. 1C

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